KK1100-FAST SWITCHING THYRISTOR

2500-2800 V_{DRM}

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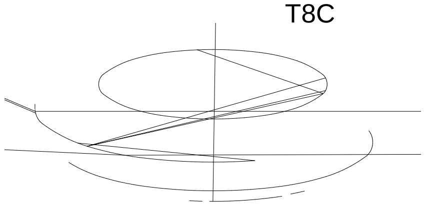
HIGH POWER THYRISTOR FOR INVERTER APPLICATION

Features:

T8C



- **All Diffused Structure**
- **Amplifying Gate Configuration**
- **Blocking capability up to 2800 volts**
- **High dv/dt Capability**
- **Pressure Assembled Device**

ELECTRICAL CHARACTERISTICS AND RATINGS

Blocking - Off State

Device Type	V_{RRM} (1)	V_{DRM} (1)	V_{RSM} (1)
KK1100/25	2500	2500	2700
KK1100/28	2800	2800	3000

V_{RRM} = Repetitive peak reverse voltage
V_{DRM} = Repetitive peak off state voltage
V_{RSM} = Non repetitive peak reverse voltage (2)

Repetitive peak reverse leakage and off state leakage	I_{RRM}/I_{DRM}	5 mA 100 mA (3)
Critical rate of voltage rise	dv/dt (4)	1000 V/μs

Conducting - On State

ELECTRICAL CHARACTERISTICS AND RATINGS KK1100-FAST SWITCHING THYRISTOR

Gating

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Peak gate power dissipatioq o ǰ						

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